

ETR16010-003

<u>XBS104V14R-G</u>

Schottky Barrier Diode, 1A, 40V Type

■FEATURES

- Forward Voltage Forward Current Repetitive Peak Reverse Voltage Environmentally Friendly
- : V_F=0.365V (TYP.)
- : I_{F(AV)}=1A
- : V_{RM}=40V
- : EU RoHS Compliant, Pb Free

■ APPLICATIONS

- Rectification
- Protection against reverse connection of battery

■ PACKAGING INFORMATION



			1a-25	
PARAMETER	SYMBOL	RATINGS	UNIT	
Repetitive Peak Reverse Voltage	Vrm	40	V	
Reverse Voltage (DC)	DC) VR 40		V	
Forward Current (Average)	IF(AV)	1	А	
Non Continuous	Ігѕм	20	А	
Forward Surge Current ^{*1}		-		
Junction Temperature	Tj	125	°C	
Storage Temperature Range	Tstg	-55 ~ 150	°C	

*1 : Non continuous high amplitude 60Hz half-sine wave.

* When the IC is operated continuously under high load conditions such as high temperature, high current and high voltage, it may have the case that reliability reduces drastically even if under the absolute maximum ratings. Adequate "Derating" should be taken into consideration while designing.



①: 0 (Product Number)
②: Assembly Lot Number

■PRODUCT NAME

PRODUCT NAME	PACKAGE
XBS104V14R-G	SOD-123A

* The "-G" suffix indicates that the products are Halogen and Antimony free as well as being fully EU RoHS compliant.

* The device orientation is fixed in its embossed tape pocket.

■ELECTRICAL CHARACTERISTICS

PARAMETER SYMBO	SVMPOL	TEST CONDITIONS	LIMITS			UNIT
	STIVIDUL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
5	VF1	I _F =100mA	-	0.23	0.315	V
	VF2	I _F =500mA	-	0.30	0.385	V
	VF3	I _F =1A	-	0.365	0.41	V
Reverse Current	IR	V _R =40V	-	0.25	2	mA
Inter-Terminal Capacity	Ct	V _R =1V , f=1MHz	-	150	-	pF
Reverse Recovery Time*2	trr	I _F =I _R =10mA , Irr=1mA	-	41	-	ns

*2 : trr measurement circuit Bias De



Ta=25°C

XBS104V14R-G

■TYPICAL PERFORMANCE CHARACTERISTICS

(1) Forward Current vs. Forward Voltage



(3) Forward Voltage vs. Operating Temperature



(5) Inter-Terminal Capacity vs. Reverse Voltage



(2) Reverse Current vs. Reverse Voltage



(4) Reverse Current vs. Operating Temperature



(6) Average Forward Current vs. Operating Temperature



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